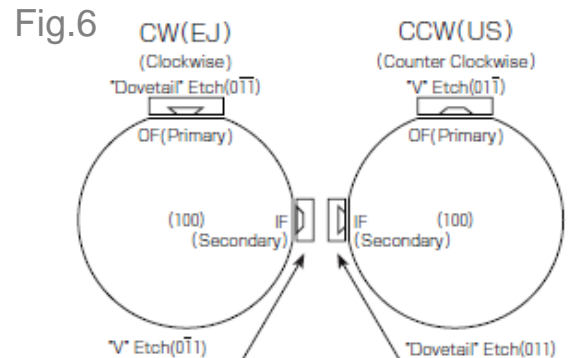
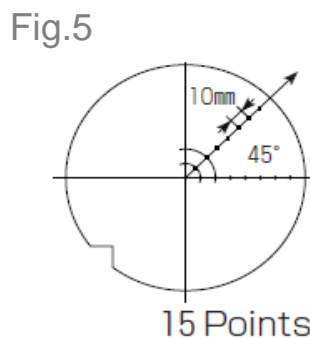
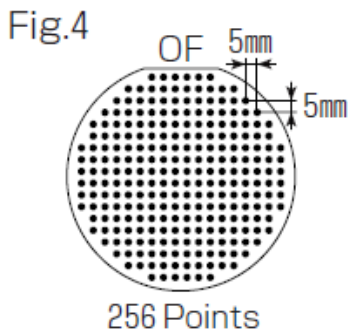
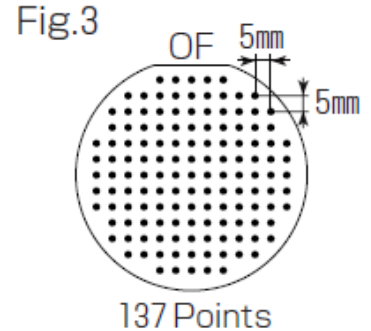
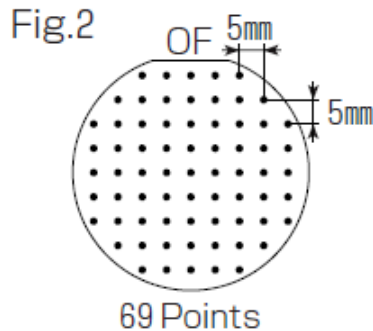
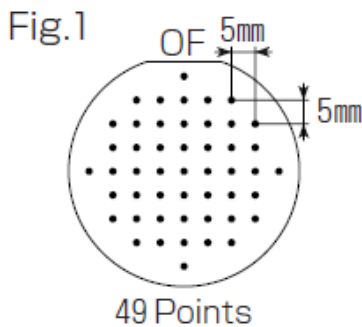


InP Single Crystal Wafers(n-Type)

Standard Specifications

Growth Method · Dopant	VB · S				VB · Sn
Carrier Concentration(cm^{-3})	$2 \sim 8 \times 10^{18}$				$1 \sim 4 \times 10^{18}$
Resistivity($\Omega \cdot \text{cm}$)	$0.6 \sim 2.5 \times 10^{-3}$				$1 \sim 6 \times 10^{-3}$
Mobility($\text{cm}^2/\text{V} \cdot \text{sec}$)	$1 \sim 2 \times 10^3$				$1.2 \sim 2.1 \times 10^3$
EPD Average(cm^{-2})	$\leq 5 \times 10^2$	$\leq 5 \times 10^3$		$\leq 1 \times 10^4$	$\leq 5 \times 10^3$
Measuring Points of EPD	Fig.2	Fig.3	Fig.4	Fig.5	Fig.1
Diameter(mm)	50.0 ± 0.3	76.0 ± 0.3	100.0 ± 0.3	150.0 ± 0.3	50.0 ± 0.3
OF(mm)(Fig. 6)(*1)	16.0 ± 1.0	22.0 ± 1.0	32.5 ± 1.0	—	16.0 ± 1.0
IF(mm)(Fig. 6)	7.0 ± 1.0	12.0 ± 1.0	18.0 ± 1.0	—	7.0 ± 1.0
Notch	—	—	—	SEMI standard	—
Edge Rounding(mmR)	0.25(Conform to SEMI Standards)				
Thickness(μm)	350 ± 15	600 ± 15	625 ± 25	675 ± 25	350 ± 15
Orientation	$(100) \pm 0.3^\circ$				
Surface Finish	P/LE, P/P		P/P		P/LE, P/P
Surface Clean(*2)	EW				
Flatness · LPD(*3)	Refer to other specification				
Package	Individual Container				



Notes

(*1) High Precision OF($\pm 0.02^\circ$) is available.

(*2) EW : Etched Wafer

(*3) LPD : Light Point Defects

Attached Data

- Standard : Resistivity, Mobility, Diameter, OF, IF, Thickness(min. ~max.), EPD Map
- Option : Accuracy of Orientation, Flatness, Light Point Defects